	Application No.	Applicant(s)	
Notice of Allowability	10/657,082	SEO, YOUNG HUN	
	Examiner	Art Unit	
	Stanetta D. Isaac	2812	
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commercements. This application is	in this application. If not included nunication will be mailed in due of	d ourse. THIS
 This communication is responsive to <u>09/09/03</u>. The allowed claim(s) is/are <u>1-8</u>. The drawings filed on <u>09 September 2003</u> are accepted by Acknowledgment is made of a claim for foreign priority ur All b) Some* c) None of the: 		or (f).	
 Certified copies of the priority documents have been received. 			
2. Certified copies of the priority documents have been received in Application No			
3. Copies of the certified copies of the priority documents have been received in this national stage application from the			
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received: 5. Acknowledgment is made of a claim for domestic priority ur reference was included in the first sentence of the specification. (a) The translation of the foreign language provisional at Acknowledgment is made of a claim for domestic priority ur in the first sentence of the specification or in an Application.	ation or in an Application Date pplication has been received ander 35 U.S.C. §§ 120 and and a second process.	ata Sheet. 37 CFR 1.78. ed. /or 121 since a specific reference	·
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.			
7. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.			
 8. CORRECTED DRAWINGS (as "replacement sheets") mus (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No. (b) including changes required by the proposed drawing or 	on's Patent Drawing Revie		omino.
(b) ☐ including changes required by the proposed drawing correction filed, which has been approved by the Examiner.(c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No			
(c) Including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No			
Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the margin according to 37 CFR 1.121(d).			
9. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FOR T	sit of BIOLOGICAL MAT HE DEPOSIT OF BIOLOG	ERIAL must be submitted. No ICAL MATERIAL.	ote the
Attachment(s)			
1⊠ Notice of References Cited (PTO-892)	5 ☐ Notice of Inf	formal Patent Application (PTO-1	52)
 2 Notice of Draftperson's Patent Drawing Review (PTO-948) 3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No. 		ımmary (PTO-413), Paper No	 •
), 7□ Examiner's A	7☐ Examiner's Amendment/Comment	
4 ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	8∭ Examiner's 9∭ Other	Statement of Reasons for Allowa	ince

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DETAILED ACTION

Allowable Subject Matter

1. Claims 1-8 are allowed.

- 2. The following is an examiner's statement of reasons for allowance: Applicant's independent claim 1 is allowed over the prior art of record because none teach or render obvious a method for fabricating a shallow trench isolation, comprising the steps of anodizing the isolation region to form a porous silicon and to form an air gap in the porous silicon, wherein a porosity of the porous silicon is determined by the dose of the implanted ion.
- 3. See Lim et al. US Patent 6,406,975 where Lim teaches forming an air gap within the shallow trench (STI) region where a cap layer is used to as an porous layer where the filler material is subjected to a plasma and heated to vaporize the filler material so that the material diffuses through the cap layer, however, fails the step of performing ion implanting process into the silicon substrate and anodizing the isolation region to form a porous silicon and to form an air gap in the porous silicon.
- 4. All dependent claims are also rendered allowable.
- 5. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."
- 6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Stanetta D. Isaac whose telephone number is 703-308-5871. The examiner can normally be reached on Monday-Friday 7:30am -5:30pm.

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7. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on 703-308-3325. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722.

8. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Stanetta Isaac Patent Examiner January 9, 2004

> Supervisory Patent Examine: Technology Center 2800